

PSMN014-80YL

N-channel 80 V, 14 mΩ logic level MOSFET in LFPAK56

14 April 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V	
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	62	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	147	W	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	12.2	15	mΩ	
Dynamic characteristics								
Q_{GD}	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	8.7	-	nC	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source	<u> </u>	
3	S	source	q j	G_U: 4
4	G	gate	و و و و	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN014-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN014-80YL	014L80

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	147	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	62	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	44	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; Fig. 4	-	250	Α
T _{stg}	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	175	°C
Source-dra	in diode		'	'		
I _S	source current	T _{mb} = 25 °C		-	62	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	250	Α
Avalanche	ruggedness		'	'		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 62 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[1][2]	-	79.6	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

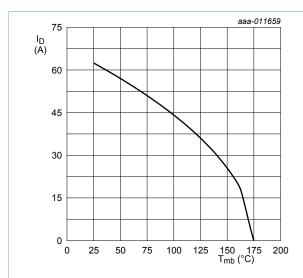


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

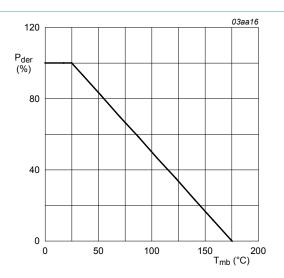


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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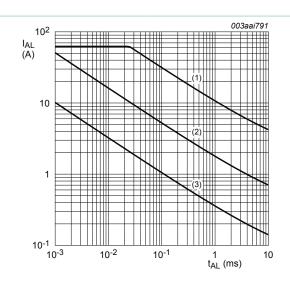


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

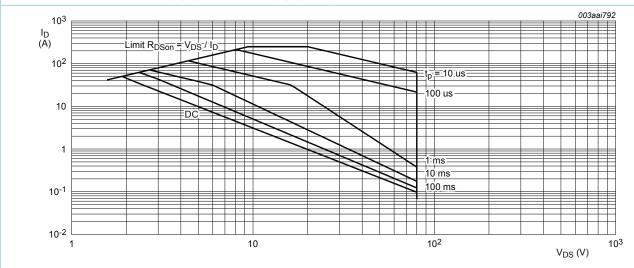


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb}$$
 = 25°C; I_{DM} is a single pulse

9. Thermal characteristics

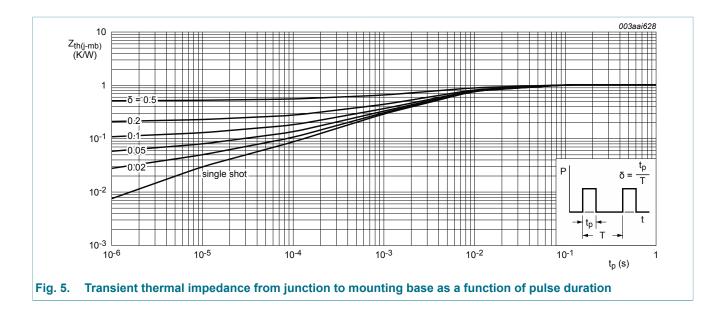
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	_	_	1.02	K/W

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10. Characteristics

Table 7. **Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		,			
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	80	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	72	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = -55 \text{ °C; } Fig. 9$	-	-	2.45	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 175 \text{ °C; } Fig. 9$	0.5	-	-	V
I _{DSS} dra	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.25	10	μΑ
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	12.2	15	mΩ
	resistance	V_{GS} = 10 V; I_D = 15 A; T_j = 25 °C; Fig. 11	-	11.3	14	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	38	mΩ
Dynamic ch	naracteristics		,	'		
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 64 V; V_{GS} = 5 V; T_j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	28.9	-	nC
		I _D = 15 A; V _{DS} = 64 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	56.9	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q_{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$		-	8.1	-	nC
Q_{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	8.7	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	3479	4640	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	236	283	pF
C _{rss}	reverse transfer capacitance			-	114	156	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R_{L} = 4 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	15.3	-	ns
t _r	rise time			-	24.6	-	ns
$t_{d(off)}$	turn-off delay time			-	45.3	-	ns
t _f	fall time			-	24.7	-	ns
Source-dra	ain diode	1					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	25.8	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$		-	29.3	-	nC

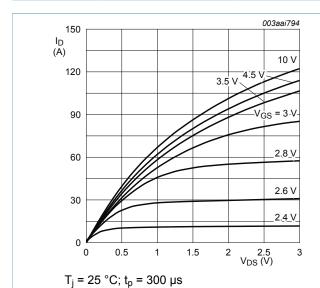


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

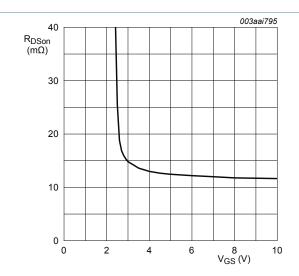


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values $T_j = 25 \,^{\circ}\text{C}; \ I_D = 15 A$

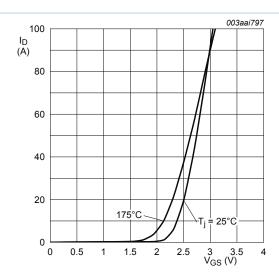


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

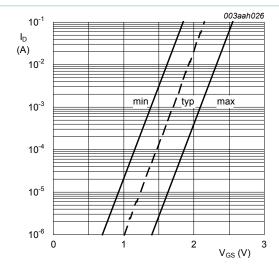


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

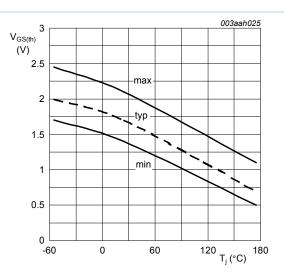
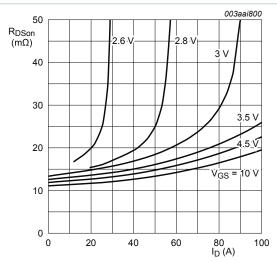


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}



 $T_j = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

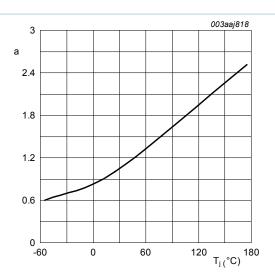


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

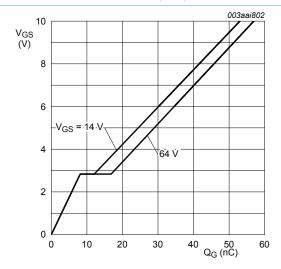


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 15A$

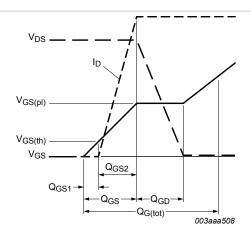


Fig. 13. Gate charge waveform definitions

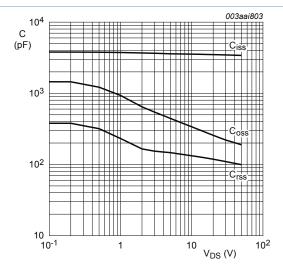


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

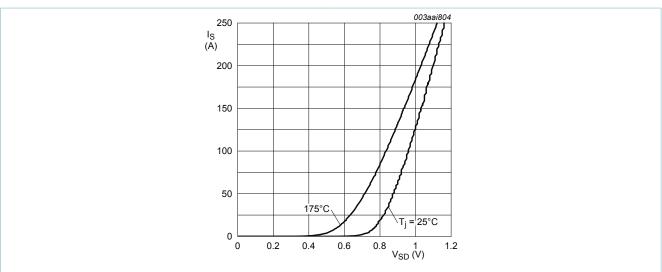


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

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11. Package outline

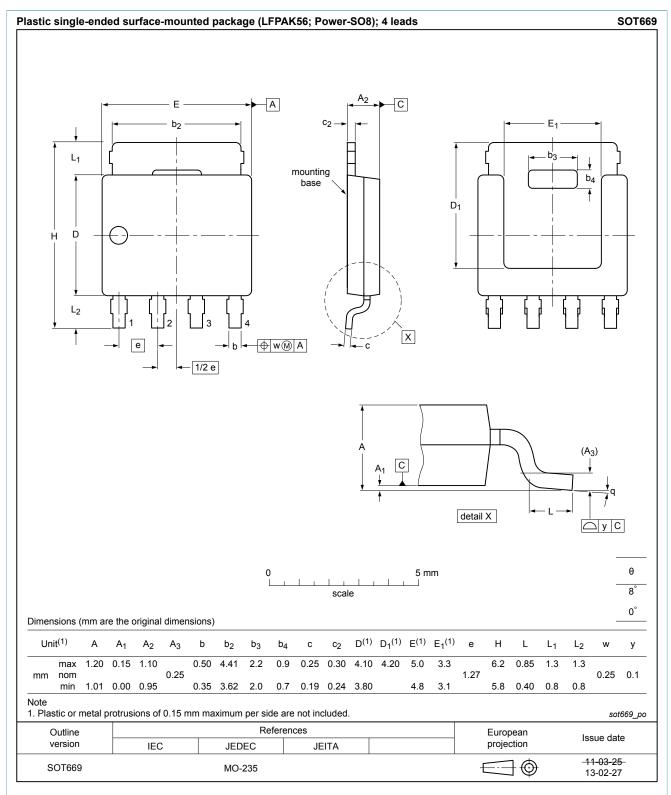


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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